

**PRODUCT CHARACTERISTICS**

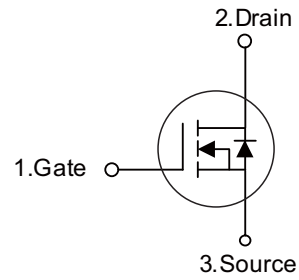
VDSS	30V
R <sub>DS(on)</sub> Typ(V <sub>GS</sub> @=4.5 V)	28mΩ
R <sub>DS(on)</sub> Typ(V <sub>GS</sub> @=2.5 V)	32mΩ
ID	4

**APPLICATIONS**

Load/Power Switching  
 Interfacing Switching

**FEATURES**

High dense cell design for extremely low R<sub>DS(ON)</sub>  
 Exceptional on-resistance and maximum DC current capability

**Symbol**

**ORDER INFORMATION**

Order codes		Package	Packing
Halogen-Free	Halogen		
N/A	MOT3400A3	SOT-23A-3L	3000pieces/Real

**ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C unless otherwise noted)**

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	30	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Continuous Drain Current	I <sub>D</sub>	4.0	A
Drain Current-Pulsed (note 1)	I <sub>DM</sub>	16	A
Power Dissipation	P <sub>D</sub>	240	mW
Thermal Resistance from Junction to Ambient (note 2)	R <sub>θJA</sub>	246	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~+150	°C

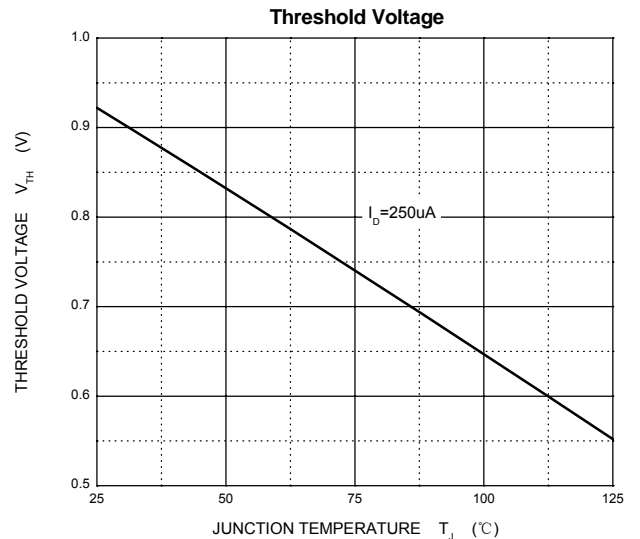
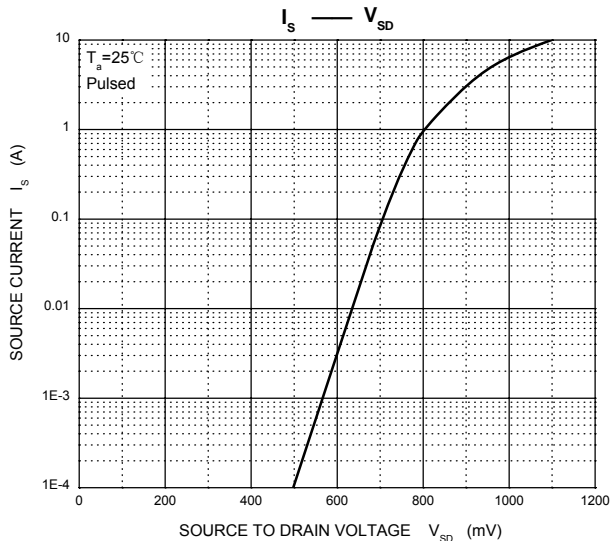
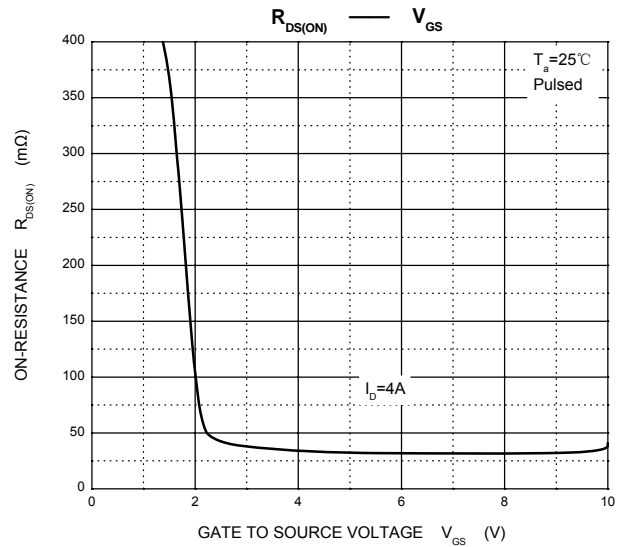
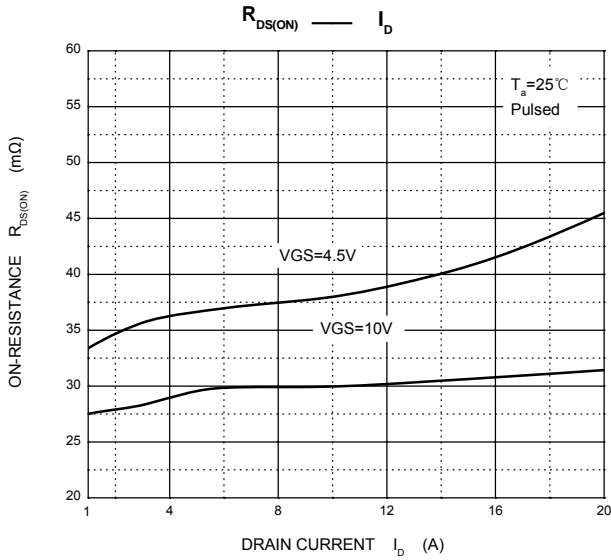
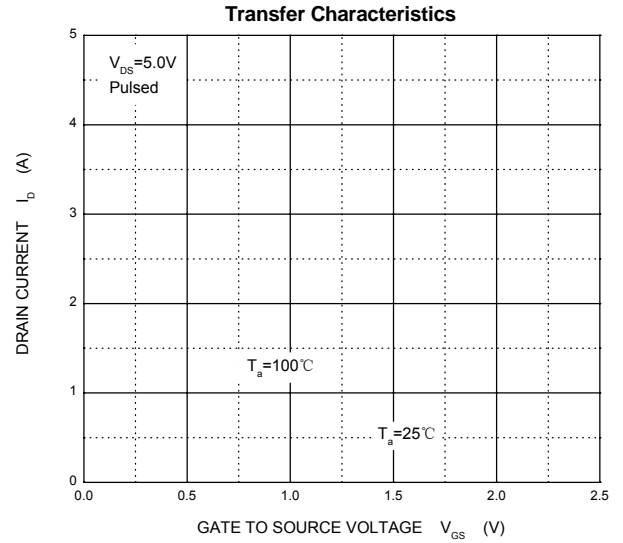
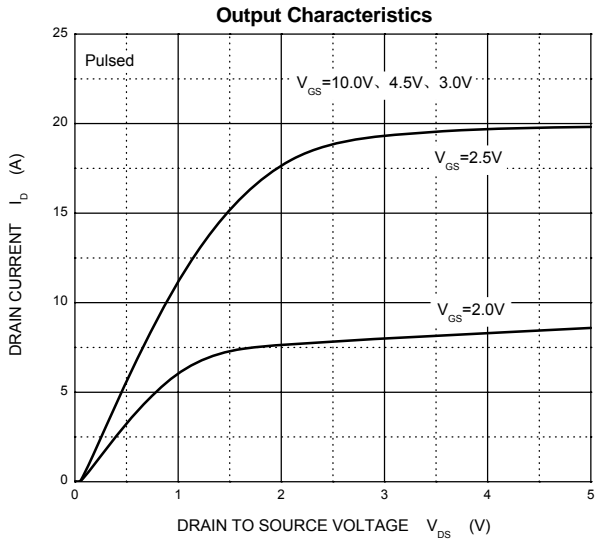
**■ ELECTRICAL CHARACTERISTICS** ( $T_C=25^\circ\text{C}$ , unless otherwise specified)

Parameter	Symbol	Test condition	Min	Typ	Max	Unit
<b>Off characteristics</b>						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	30	-	-	V
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = 24V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate-source leakage current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0V$	-	-	$\pm 100$	nA
<b>On characteristics</b>						
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 4.5V, I_D = 3A$	-	28	40	m $\Omega$
		$V_{GS} = 2.5V, I_D = 2A$	-	32	54	m $\Omega$
Forward transconductance	$g_{FS}$	$V_{DS} = 5V, I_D = 4A$	8	-	-	S
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	0.7	-	1.4	V
<b>Dynamic characteristics</b>						
Input capacitance	$C_{iss}$	$V_{DS} = 15V, V_{GS} = 0V, f = 1MHz$	-	-	1050	pF
Output capacitance	$C_{oss}$		-	99	-	pF
Reverse transfer capacitance	$C_{rss}$		-	77	-	pF
Gate resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	-	-	3.6	$\Omega$
<b>Switching characteristics</b>						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 15V,$ $R_L = 2.7\Omega, R_{GEN} = 3\Omega$	-	-	5	ns
Turn-on rise time	$t_r$		-	-	7	ns
Turn-off delay time	$t_{d(off)}$		-	-	40	ns
Turn-off fall time	$t_f$		-	-	6	ns
<b>Drain-source diode characteristics</b>						
Diode forward voltage	$V_{SD}$	$I_S = 2.9A, V_{GS} = 0V$	-	-	1	V

**Note :**

1. Repetitive Rating : Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t < 5$  sec.
3. Pulse Test : Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production testing.

■ TYPICAL CHARACTERISTICS



■ SOT-23A-3L PACKAGE OUTLINE DIMENSIONS

